

# **P-Channel Power MOSFET**

-30V, -3A, 60mΩ

## **Features**

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low Onresistance
- Pb-free plating
- RoHS compliant
- Halogen-free package

## **Application**

- Load Switch
- PA Switch

KEY PERFORMANCE PARAMETERS					
PARAN	IETER	VALUE	UNIT		
VD	s	-30	V		
R <sub>DS(on)</sub> (max)	$V_{GS} = -10V$	60			
	$V_{GS} = -4.5V$	90	mΩ		
Qg		9.52	nC		







P-Channel MOSFET

Drain Pin 2

Notes: Moisture sensitivity level: level 3. Per J-STD-020

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>A</sub> = 25°C unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage	V <sub>DS</sub>	-30	V			
Gate-Source Voltage	V <sub>GS</sub>	±20	V			
Continuous Drain Current (Note 1)	$T_A = 25^{\circ}C$	I <sub>D</sub>	-3	A		
Pulsed Drain Current (Note 2)	I <sub>DM</sub>	-10	А			
Continuous Source Current (Diode Conduction	I <sub>S</sub>	-1.9	А			
Total Power Dissipation	$T_A = 25^{\circ}C$	P <sub>DTOT</sub>	Р <sub>ртот</sub> 1.6			
Operating Junction and Storage Temperature F	T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150	°C			

THERMAL PERFORMANCE						
PARAMETER	SYMBOL	LIMIT	UNIT			
Junction to Case Thermal Resistance	R <sub>eJC</sub>	75	°C/W			
Junction to Ambient Thermal Resistance	R <sub>OJA</sub>	250	°C/W			

**Notes:**  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\Theta JA}$  is guaranteed by design while  $R_{\Theta CA}$  is determined by the user's board design.  $R_{\Theta JA}$  shown below for single device operation on FR-4 PCB in still air.



Taiwan Semiconductor

PARAMETER	CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNIT	
Static (Note 3)	I			1		1	
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = -250 \mu A$	BV <sub>DSS</sub>	-30			V	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	V <sub>GS(TH)</sub>	-1.0	-1.5	-3.0	V	
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA	
Zero Gate Voltage Drain Current	$V_{DS} = -24V, V_{GS} = 0V$	I <sub>DSS</sub>			-1	μA	
On-State Drain Current	$V_{DS} = -5V, V_{GS} = -10V$	I <sub>D(ON)</sub>	-6			А	
Davia Courses On Otata Daviatana	$V_{GS} = -10V, I_{D} = -3A$	P		50	60	mΩ	
Drain-Source On-State Resistance	$V_{GS} = -4.5V, I_{D} = -2A$	R <sub>DS(ON)</sub>		75	90		
Forward Transconductance	$V_{DS} = -15V, I_{D} = -5A$	<b>g</b> <sub>fs</sub>	4	7		S	
Dynamic (Note 4)							
Total Gate Charge		Qg		9.52			
Gate-Source Charge	$V_{DS} = -15V, I_D = -3A,$	Q <sub>gs</sub>		3.43		nC	
Gate-Drain Charge	V <sub>GS</sub> = -10V	$Q_gd$		1.71			
Input Capacitance		C <sub>iss</sub>		551.57			
Output Capacitance	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz	C <sub>oss</sub>		90.96		pF	
Reverse Transfer Capacitance		C <sub>rss</sub>		60.79			
Switching (Note 5)							
Turn-On Delay Time		t <sub>d(on)</sub>		10.8			
Turn-On Rise Time	$V_{DD} = -15V,$	t <sub>r</sub>		2.33		ns	
Turn-Off Delay Time	$R_{GEN} = 6\Omega,$ $I_D = -1A, V_{GS} = -10V,$	t <sub>d(off)</sub>		22.53			
Turn-Off Fall Time	$U = -i\Lambda, v_{GS} = -iUv,$	t <sub>f</sub>		3.87			
Source-Drain Diode (Note 3)							
Forward On Voltage	I <sub>S</sub> = -1.9 A, V <sub>GS</sub> = 0V	V <sub>SD</sub>		-0.8	-1.3	V	

Notes:

1. Pulse width limited by the maximum junction temperature.

2. Surface Mounted on FR4 Board,  $t \le 5$  sec.

3. Pulse test: PW  $\leq$  300µs, duty cycle  $\leq$  2%.

4. For DESIGN AID ONLY, not subject to production testing.

5. Switching time is essentially independent of operating temperature.



### **ORDERING INFORMATION**

PART NO.	PACKAGE	PACKING
TSM3401CX RFG	SOT-23	3,000pcs / 7"Reel

Note:

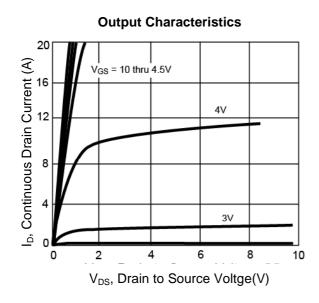
1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC

2. Halogen-free according to IEC 61249-2-21 definition

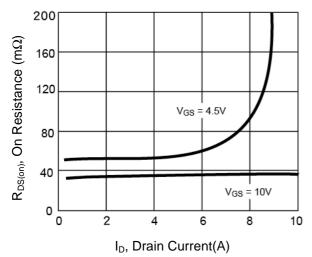


## **CHARACTERISTICS CURVES**

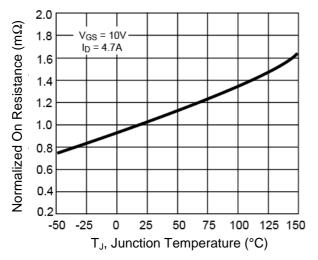
 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

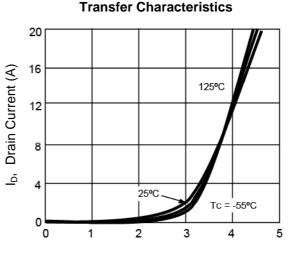


**On-Resistance vs. Drain Current** 



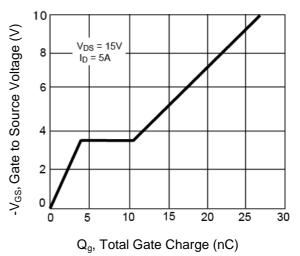
**On-Resistance vs. Junction Temperature** 



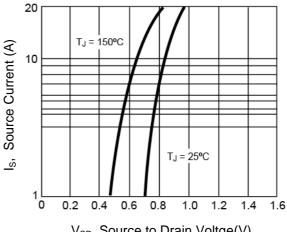


V<sub>GS</sub>, Gate to Source Voltge(V)

**Gate Charge** 



Source-Drain Diode Forward Voltage

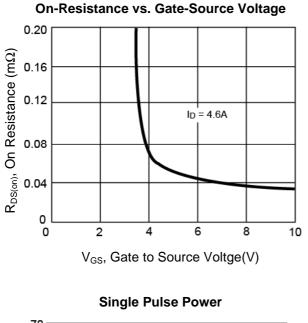


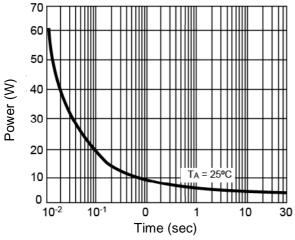
V<sub>SD</sub>, Source to Drain Voltge(V)

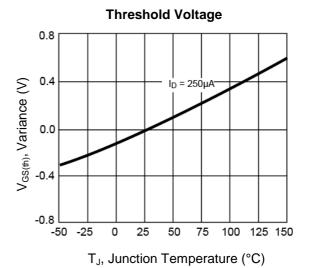


# **CHARACTERISTICS CURVES**

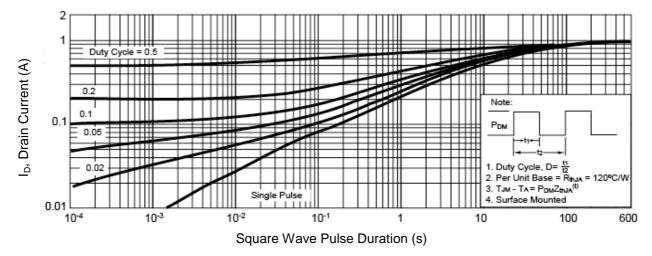
 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 







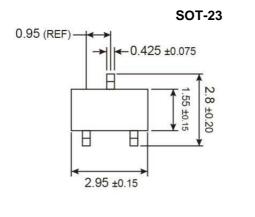
Normalized Thermal Transient Impedance Curve

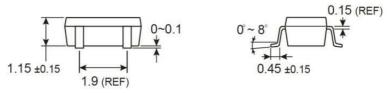




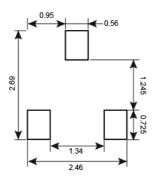


## PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

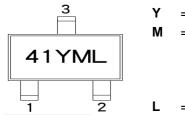




#### SUGGESTED PAD LAYOUT (Unit: Millimeters)



### **MARKING DIAGRAM**



Y	= Year	Code						
Μ	= Month Code for Halogen Free Product							
	0	=Jan	Ρ	=Feb	Q	=Mar	R	=Apr
	S	=May	Т	=Jun	U	=Jul	V	=Aug
	W	=Sep	Х	=Oct	Υ	=Nov	Ζ	=Dec
L	= Lot C	Code (1-	-9, A	A~Z)				



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